



# MRF234

## NPN SILICON RF POWER TRANSISTOR

### DESCRIPTION:

The **ASI MRF234** is Designed for Large-Signal Amplifier Applications to 100 MHz.

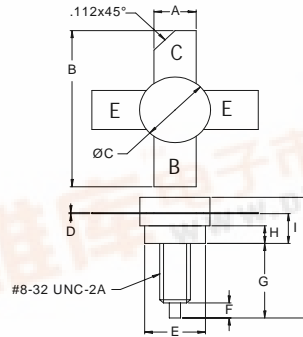
### FEATURES:

- Common Emitter
- **Omnigold™** Metalization System
- $P_G = 9.5 \text{ dB min. at } 25 \text{ W/ } 90 \text{ MHz}$

### MAXIMUM RATINGS

$I_C$	4.0 A
$V_{CE}$	18 V
$V_{CB}$	36 V
$P_{DISS}$	70 W @ $T_C = 25 \text{ }^\circ\text{C}$
$T_J$	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
$T_{STG}$	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$\theta_{JC}$	2.5 $^\circ\text{C/W}$

### PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

### CHARACTERISTICS $T_C = 25 \text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 200 \text{ mA}$	36			V
$BV_{CEO}$	$I_C = 200 \text{ mA}$	18			V
$BV_{EBO}$	$I_E = 5.0 \text{ mA}$	4.0			V
$I_{CBO}$	$V_{CB} = 15 \text{ V}$			1.0	mA
$h_{FE}$	$V_{CE} = 5.0 \text{ V}$ $I_C = 1.0 \text{ A}$	5.0			---
$C_{ob}$	$V_{CB} = 12.5 \text{ V}$ $f = 1.0 \text{ MHz}$		100	120	pF
$G_{PE}$	$V_{CC} = 12.5 \text{ V}$ $P_{out} = 25 \text{ W}$ $f = 90 \text{ MHz}$	9.5			dB
$\eta$		55			%

